

ME20VZ1UAB

1. Features

- 558 Watts peak pulse power ($t_p = 8/20\mu s$)
- Uni-directional configurations
- Solid-state silicon-avalanche technology
- Capacitance: 35pF typical
- Low clamping voltage
- Low leakage current
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30KV$
 - Contact discharge: $\pm 30KV$
 - IEC61000-4-4 (EFT) 40A (5/50ns)
 - IEC61000-4-5(Lightning) 18A (8/20us)

2. Application

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals

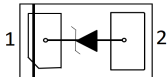
3. Mechanical Data

- Package: DFN1006-2L
- UL Flammability Classification Rating 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

4. Absolute Maximum Rating

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30 ± 30	KV
Peak Pulse Power(8/20 μs)	P_{PP}	558	W
Reverse Working Voltage	V_{RWM}	20	V
Maximum Reverse Peak Pulse Current	I_{PP}	18	A
Operating Temperature	T_{OPT}	-55~+125	°C
Storage Temperature	T_{stg}	-55~+150	°C

5. Pinning information

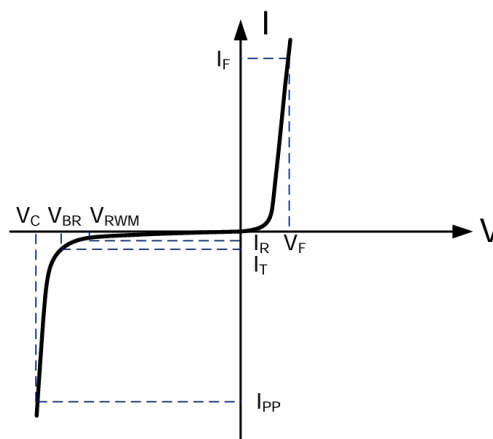
Pin	Symbol	Simplified outline	Equivalent Circuit	Marking	Package
2	Uni			DZ	DFN1006-2L

6. Electrical Characteristics (T_{amb}=25°C)

Parameter	Symbols	Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}				20	V
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	22			V
Reverse Leakage Current	I _R	V _{RWM} =20V			1	uA
Clamping Voltage	V _C	I _{pp} =18A, t _p =8/20us		28	31	V
Junction Capacitance	C _J	V _R =0V, f=1MHz		35		pF

7. Electrical Parameters

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage@I _{PP}
V _{RWM}	Reverse Working Voltage
I _R	Maximum Reverse Leakage Current
I _T	Test Current
V _{BR}	Breakdown Voltage@I _T
V _F	Forward Voltage
I _F	Forward Test Current



8. Typical Characteristics

Fig.1 8/20 μ s Waveform Per IEC6100-4-5

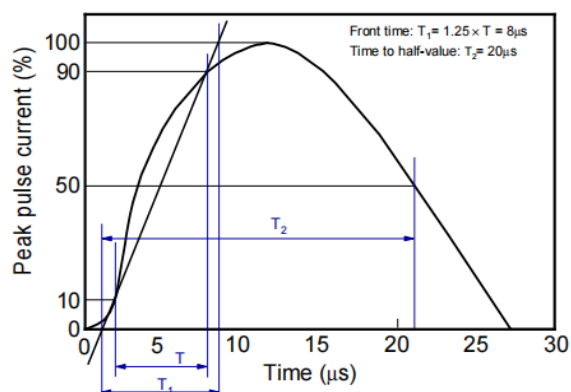


Fig.2 Contact Discharge Current Waveform per IEC61000-4-2

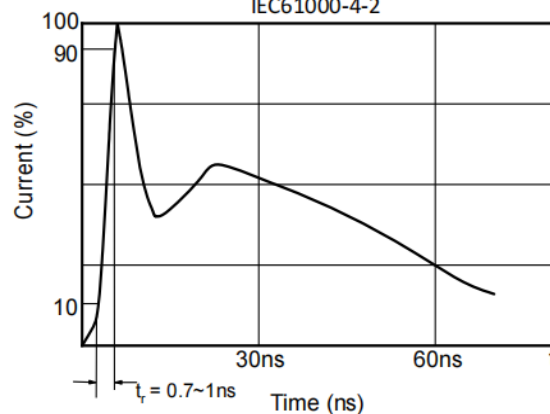


Fig.3 Clamping Voltage Vs. Peak Pulse Current

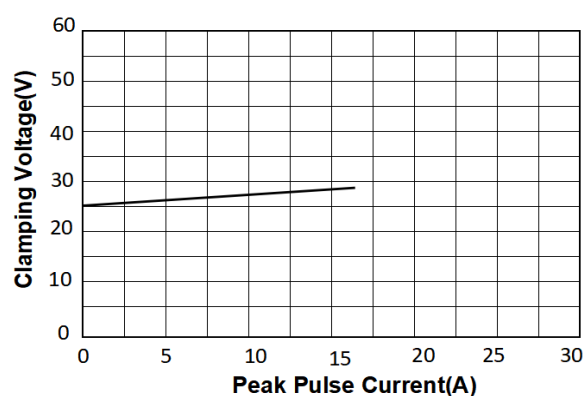
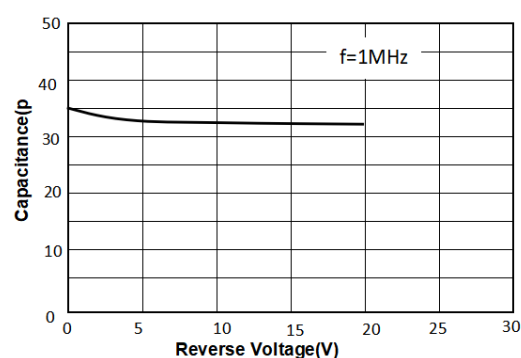
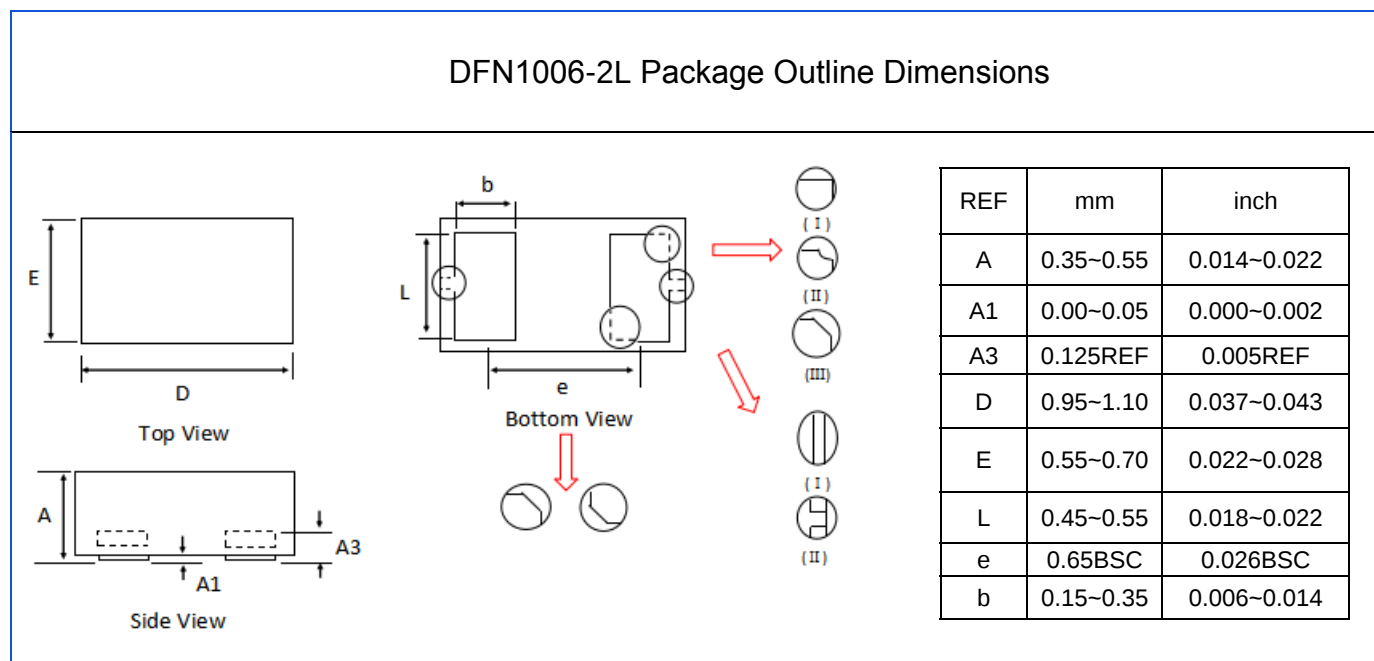


Fig.4 Capacitance VS Reverse Voltage



9.Outline Drawing



10. Reel packing

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	QTY/Box (pcs)	Q'TY/Carton (pcs)
DFN1006-2L	7'	178	10,000	100,000	400,000

11.Important Notice and Disclaimer

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